

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE6005AN uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

● V_{DS}=60V,I_D=5A

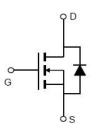
 $R_{DS(ON)}$ <30m Ω @ V_{GS} =10V (Typ.26m Ω)

 $R_{DS(ON)}$ <38m Ω @ V_{GS} =4.5V (Typ.32m Ω)

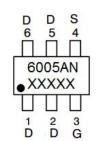
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

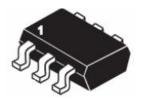
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Schematic diagram



Marking and pin assignment



SOT23-6L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
6005AN	NCE6005AN-S	SOT23-6L	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous	I _D	5	А
Drain Current-Continuous(T _C =100 ℃)	I _D (100℃)	3.5	А
Pulsed Drain Current	I _{DM}	24	Α
Maximum Power Dissipation	P _D	2	W
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	Reja	62.5	°C/W	ĺ
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Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20 V , V_{DS} =0 V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.2	1.6	2.5	V
Dunin Course On State Besistance	R _{DS(ON)}	V _{GS} =10V, I _D =5A	-	26	30	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =5A	60 -	32	38	mΩ
Forward Transconductance	G FS	V _{DS} =5V,I _D =5A	11	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	Clss	V _{DS} =30V,V _{GS} =0V, F=1.0MHz	-	979	-	PF
Output Capacitance	Coss		-	120	-	PF
Reverse Transfer Capacitance	C _{rss}		-	100	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	10	-	nS
Turn-on Rise Time	tr	V_{DD} =30V, R_L =6.7 Ω	-	3	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =3 Ω	-	21	-	nS
Turn-Off Fall Time	t _f		-	5	-	nS
Total Gate Charge	Qg	.,	-	22		nC
Gate-Source Charge	Q _{gs}	V _{DS} =30V,I _D =5A,	-	3.3		nC
Gate-Drain Charge	Q_{gd}		5.2		nC	
Drain-Source Diode Characteristics			•			,
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =5A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	5	А

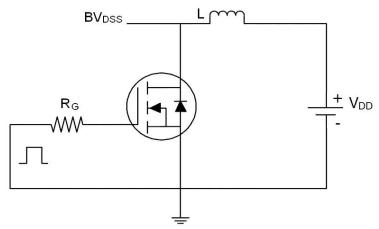
Notes

- **1.** Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2\%$.
- **4.** Guaranteed by design, not subject to production
- **5.** EAS condition:Tj=25 $^{\circ}$ C,VDD=30V,VG=10V,L=0.5mH,Rg=25 Ω

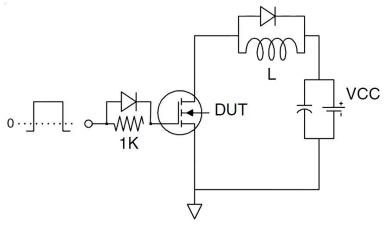


Test Circuit

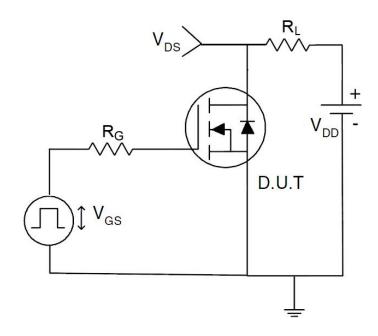
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit







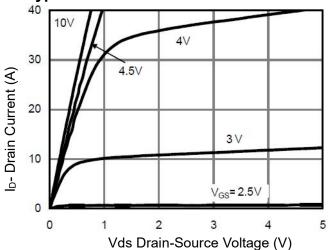


Figure 1 Output Characteristics

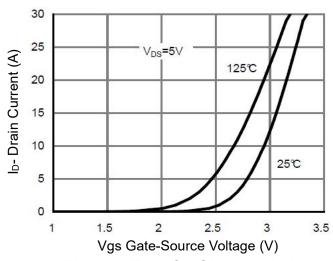


Figure 2 Transfer Characteristics

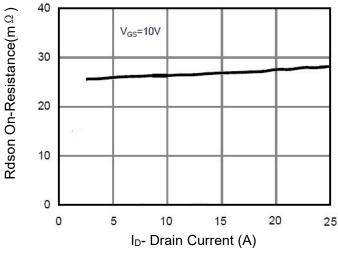


Figure 3 Rdson- Drain Current

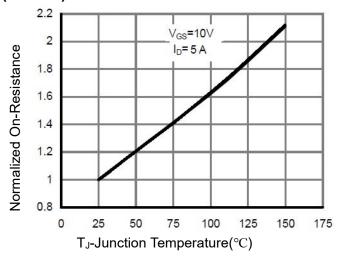


Figure 4 Rdson-Junction Temperature

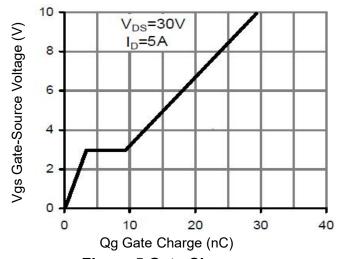


Figure 5 Gate Charge

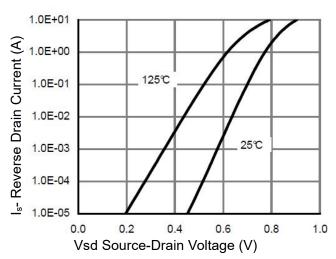


Figure 6 Source- Drain Diode Forward



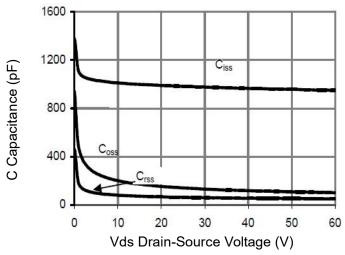


Figure 7 Capacitance vs Vds

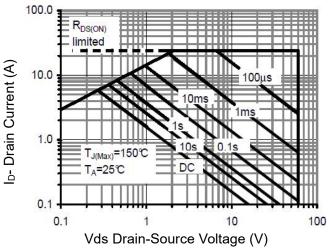


Figure 8 Safe Operation Area

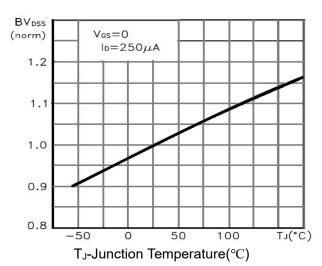


Figure 9 BV_{DSS} vs Junction Temperature

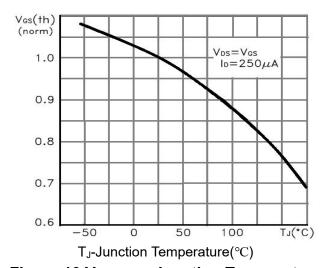


Figure 10 V_{GS(th)} vs Junction Temperature

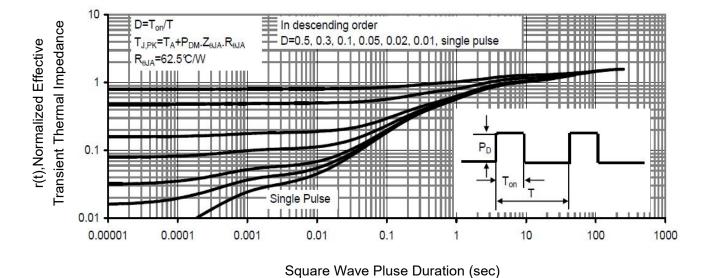
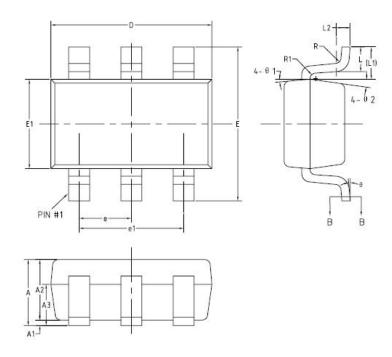


Figure 11 Normalized Maximum Transient Thermal Impedance

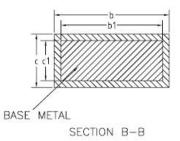


SOT23-6L Package Information

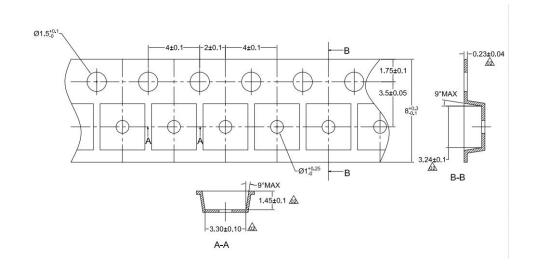


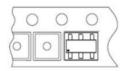
COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX	
Α		-	1.45	
A1	0	_	0.15	
A2	0.90	1.10	1.30	
A3	0.60	0.65	0.70	
b	0.39	_	0.49	
b1	0.38	0.40	0.45	
С	0.12		0.19	
c1	0.11	0.13	0.15	
D	2.85	2.95	3.05	
E	2.60	2.80	3.00	
E1	1.55	1.65	1.75	
e	0.85	0.95	1.05	
e1	1.80	1.90	2.00	
L	0.35	0.45	0.60	
L1		0.59REF		
L2	0.25BSC			
R	0.05		_	
R1	0.05	-	0.20	
θ	0.	_	8*	
θ 1	8*	10°	12*	
θ 2	8°	10°	12°	











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NCE6005AN

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